

Infineon

A new method to reduce artefacts during TEM sample preparation using FIB

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Failure Analysis



Never stop thinking

A new method to reduce artefacts during TEM sample preparation

- n Motivation
- n Amorphization
- n Curtaining effect
- n Optimized sample preparation
- n TEM Imaging
- n Conclusion

Motivation

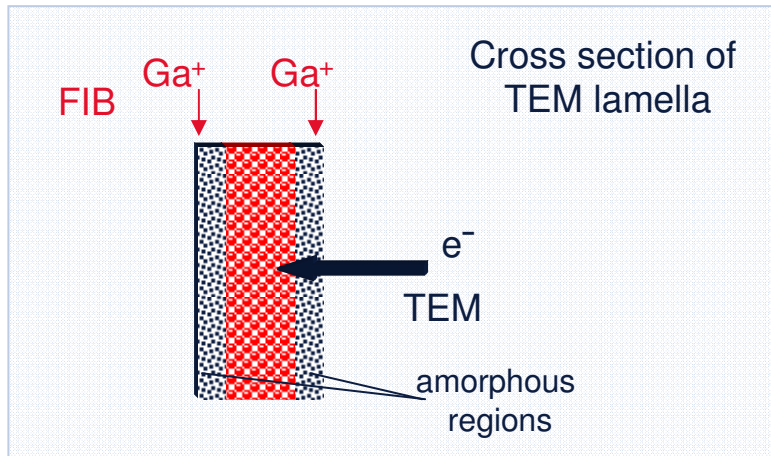
- n Quality of the sample essential for high resolution TEM imaging

- n FIB induced preparation artefacts like
 - Amorphization
 - Curtaining effectshave to be reduced

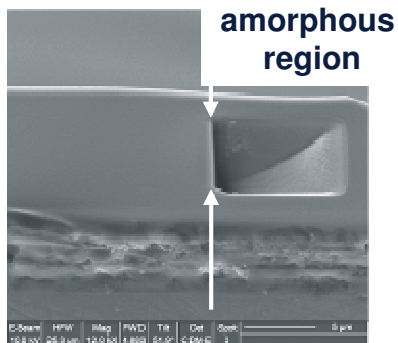
➔ Demand for an optimized TEM sample preparation

Amorphization

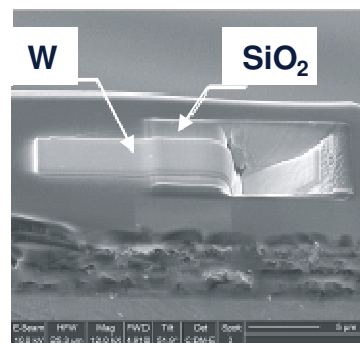
- n Low kV thinning to reduce amorphous layers



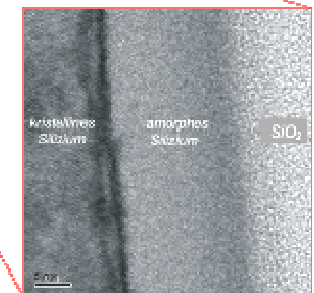
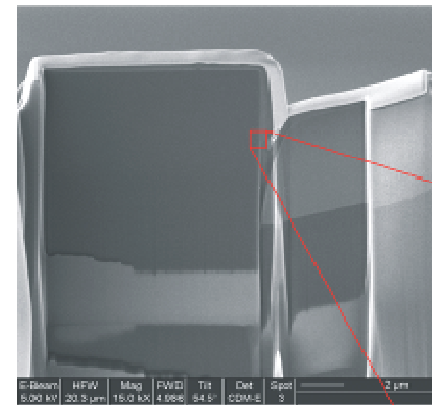
Procedure of sample preparation:



Ga⁺ ion implantation :
30 kV 5 kV



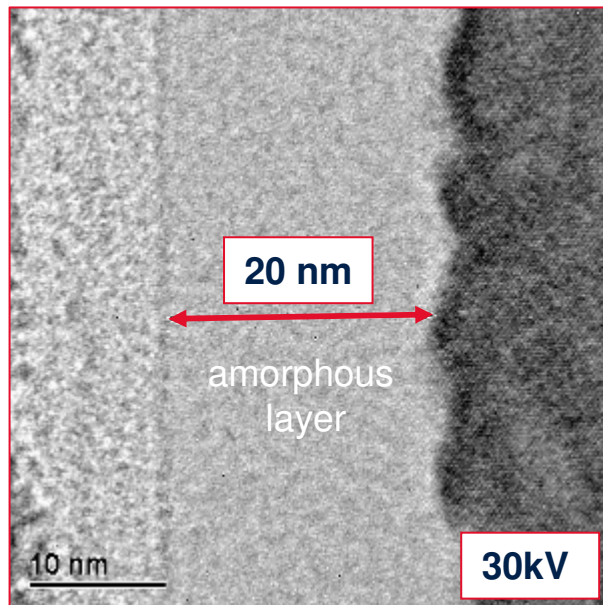
Electron induced SiO₂ deposition and ion induced W deposition



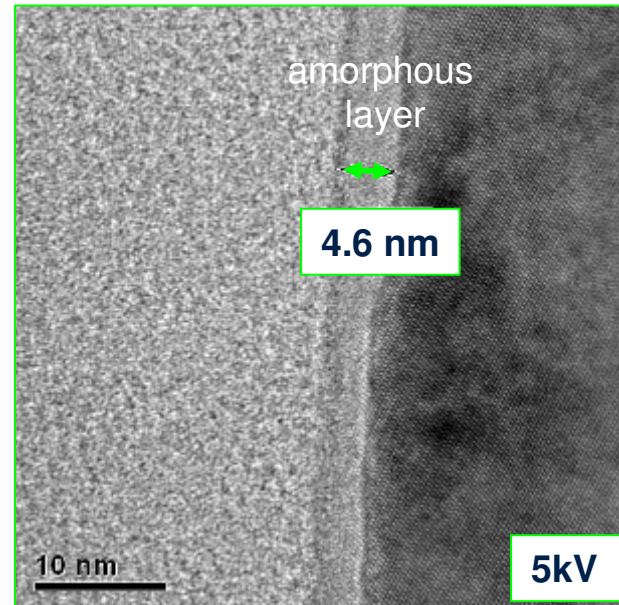
HR TEM image

Amorphization

- n Low kV thinning to reduce amorphous layers



Conventional TEM, not suitable for High Resolution (HR)



Good for HR imaging

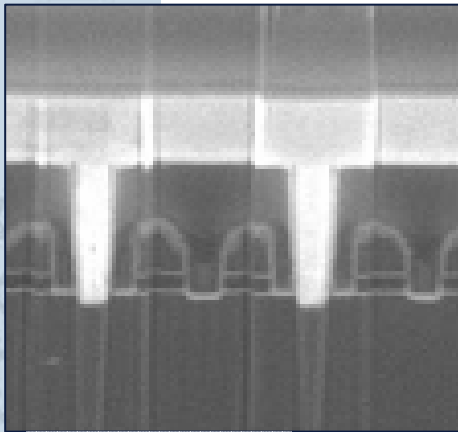
good results with low kV
20nm 4.6nm

Drawback: strong curtaining effects during low kV thinning

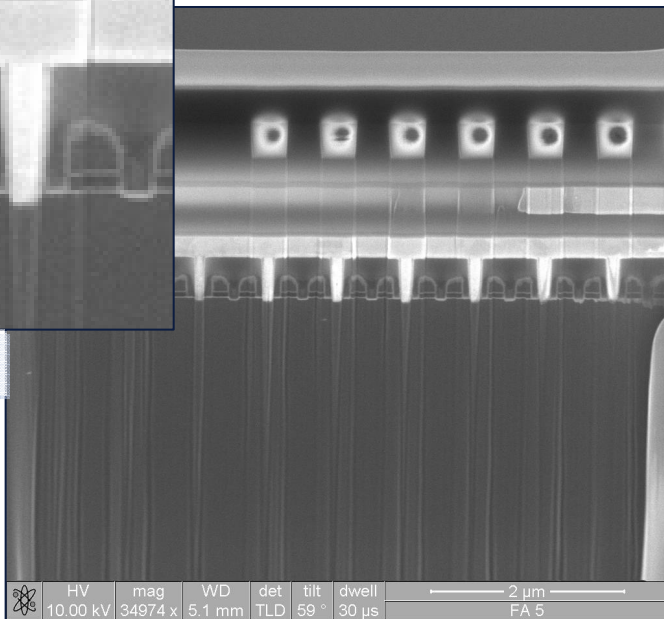
Curtaining

- n Strong curtaining effect using low kV
 - caused by different material and sputter rates

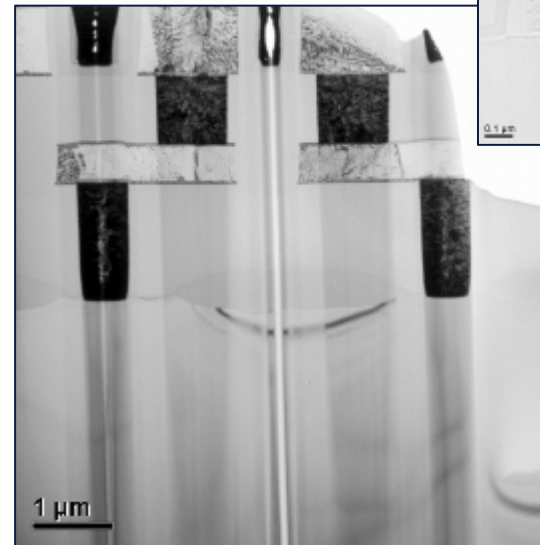
➔ interfering variations in sample thickness



SEM Images

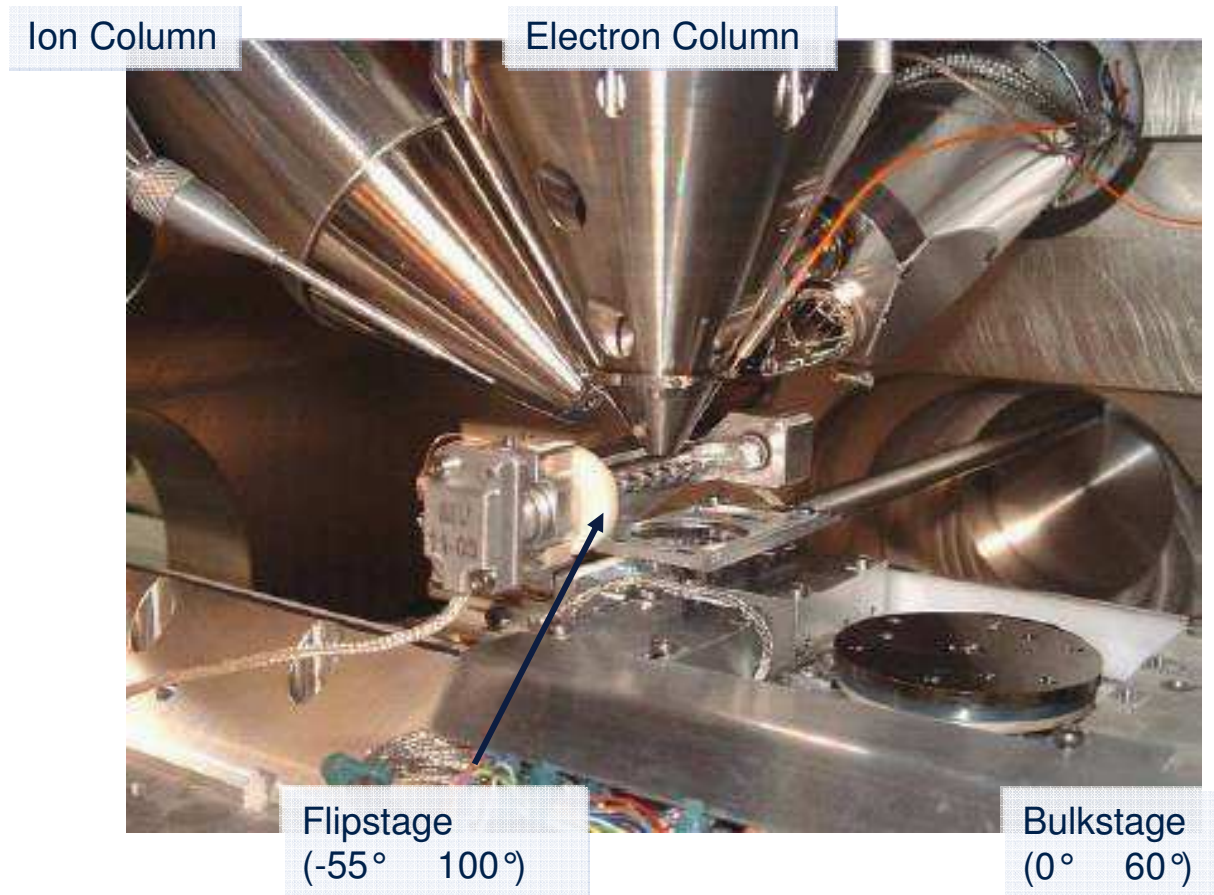


TEM Images



Optimized TEM sample preparation

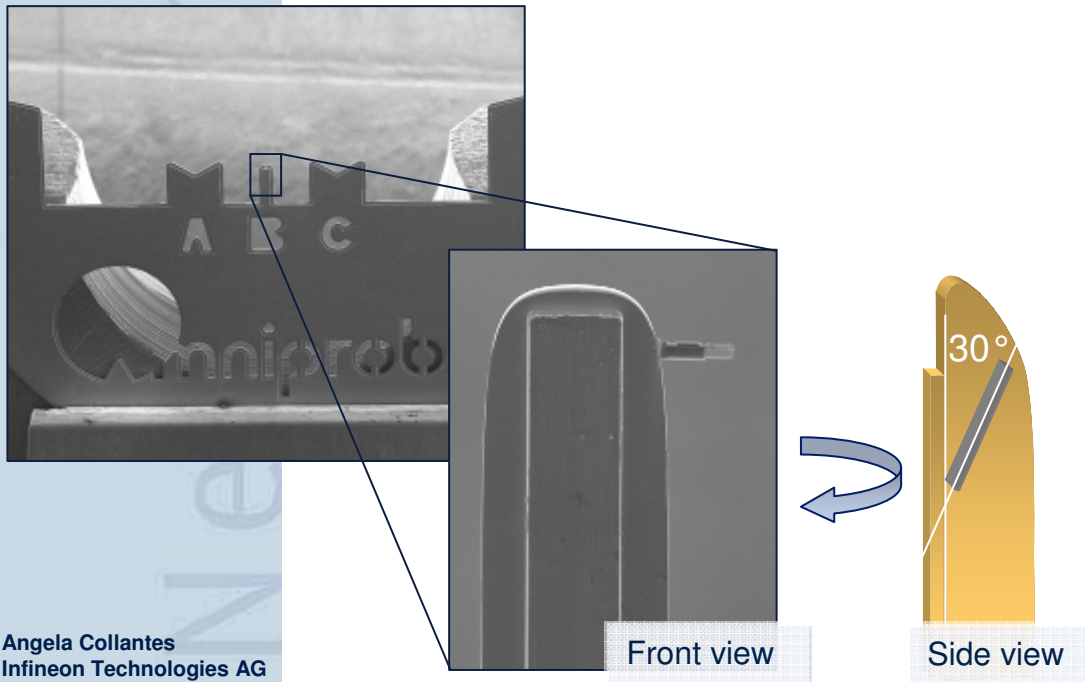
n Geometry of stages



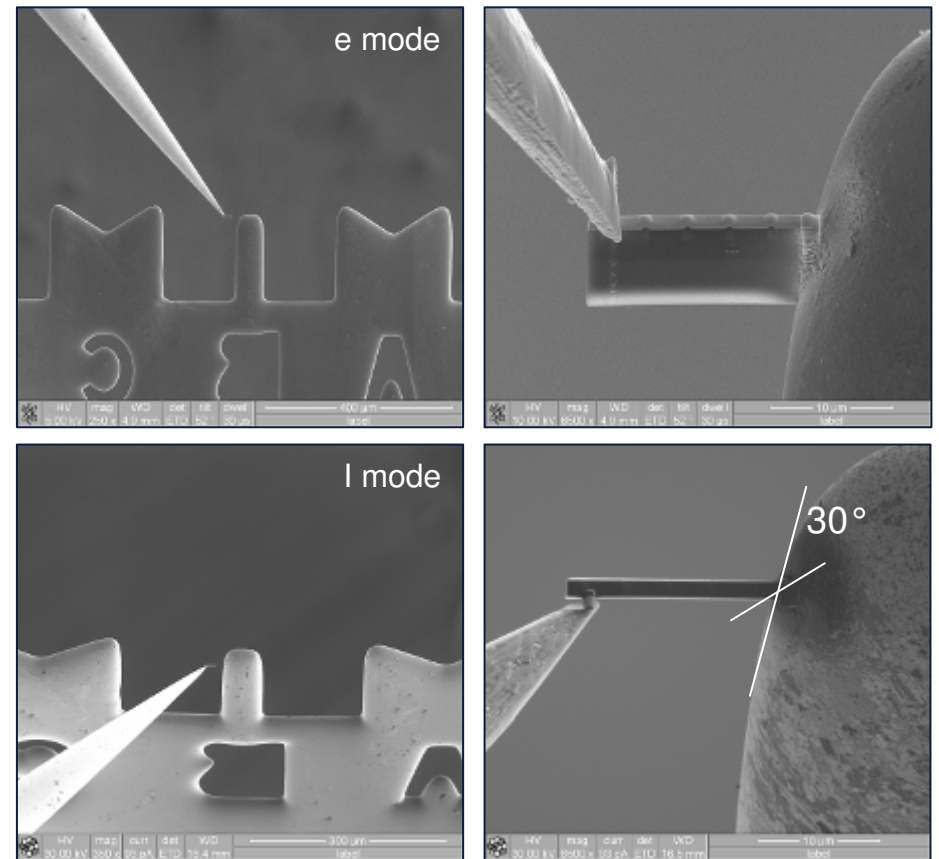
Optimized TEM sample preparation

n Lift Out:

- Attaching of lamella to grid at 30°
- Bulkstage = 52°
- Flipstage = -30°



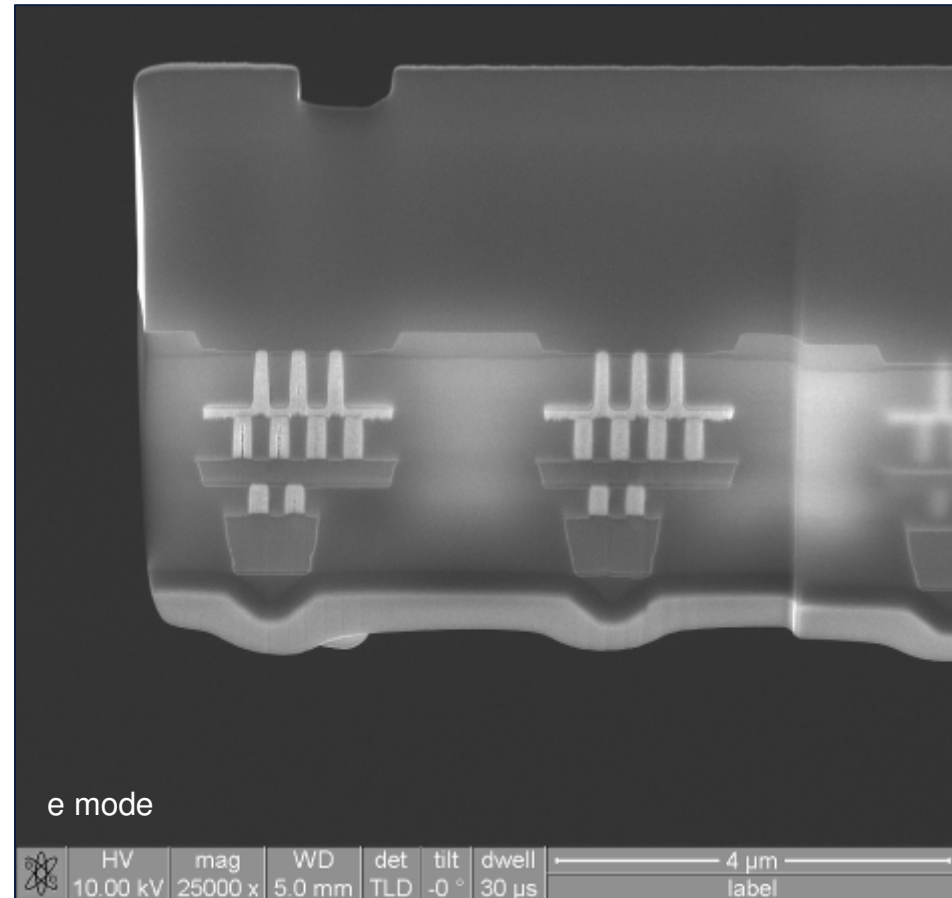
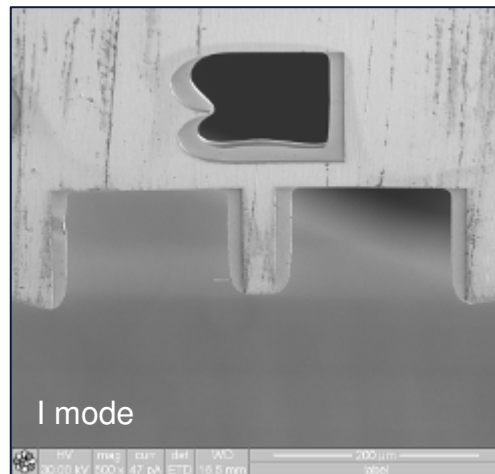
Grid with TEM lamella



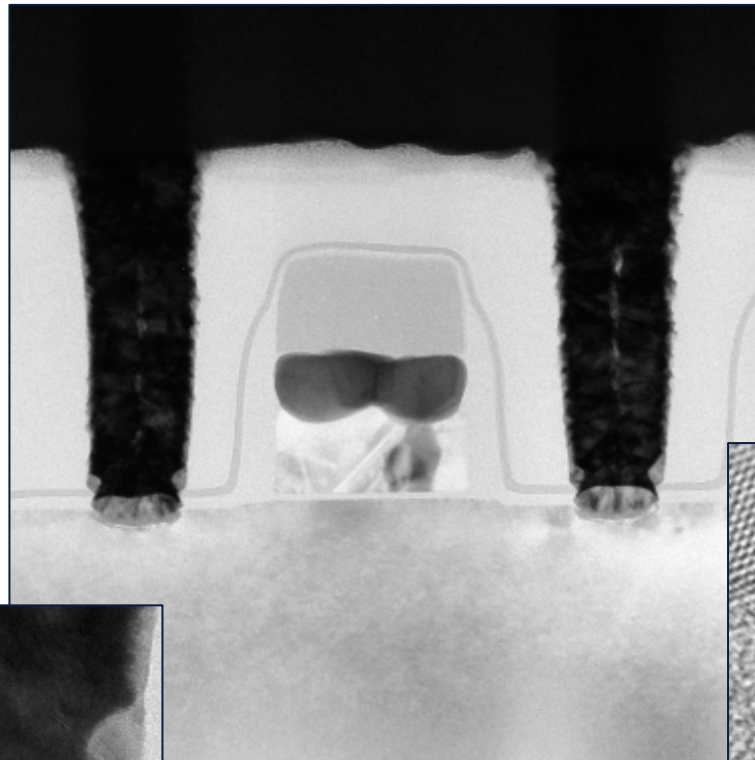
Optimized TEM sample Preparation

n Final thinning :

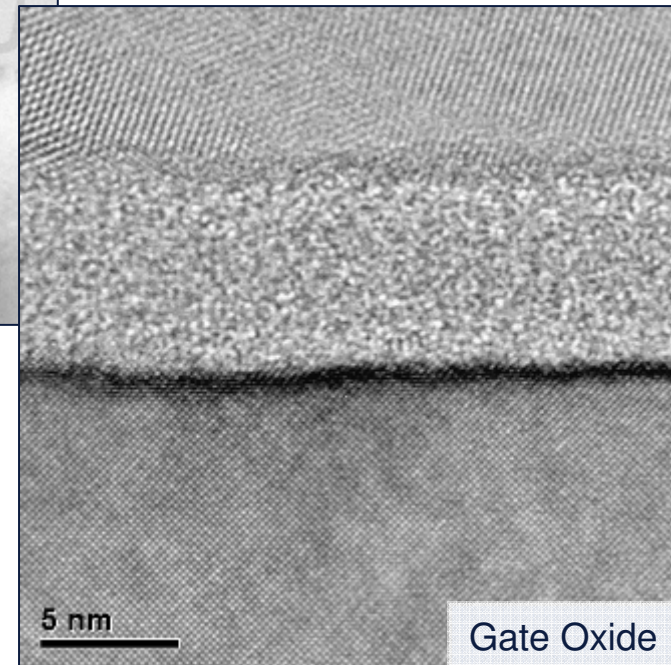
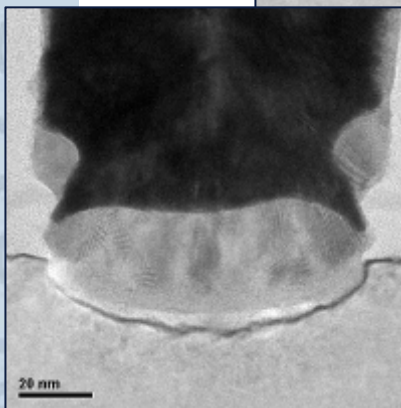
- at 5kV to minimize Ga⁺ implant
- upside down to avoid curtaining
- Bulkstage = 0°
- Flipstage = 98°



TEM Imaging



Good results with low kV
and thinning from backside
reduced amorphization
no curtaining



Conclusion

- n A new method of TEM sample preparation was found
- n Preparation artefacts such as FIB induced damage and curtaining effects were minimized
- n Whole procedure is performed inside the FIB without additional handling of the sample
- n Same time effort as for conventional preparation